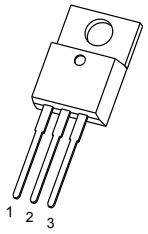
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-220-3L Plastic-Encapsulate MOSFETS

CJP04N60 600V N-Channel Power MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$MAX	I_D
600V	3Ω@10V	4A

TO-220-3L



1. GATE
2. DRAIN
3. SOURCE

General Description

This advanced high voltage MOSFET is designed to wighstand high energy in the avalanche mode and switch efficiently. This new high energy device also offers a drain-to-source diode wigh fast recovery time. Desighed for high voltage, high speed switching applications such as power supplies, converters, power motor controls and bridge circuits.

FEATURE

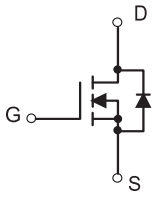
- High Current Rating
- Lower $R_{ds(on)}$
- Lower Capacitance
- Lower Total Gate Charge
- Tighter VSD Specifications
- Avalanche Energy Specified

MARKING



CJP04N60= Device code
Solid dot = Green molding compound device, if none, the normal device
XXX=Date Code

EQUIVALENT CIRCUIT



Maximum ratings (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Units
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GSS}	±30	
Continuous Drain Current	I_D	4.0	A
Continuous Drain-Source Diode Forward Current	I_S	4.0	
Single Pulsed Avalanche Energy (note1)	E_{AS}	260	mJ
Thermal Resistance fromJunction to Ambient	$R_{\theta JA}$	62.5	℃/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 ~+150	℃
Maximum lead temperure for soldering purposes , 1/8”from case for 5 seconds	T_L	260	

MOSFET ELECTRICAL CHARACTERISTICS

T_a=25℃ unless otherwise specified

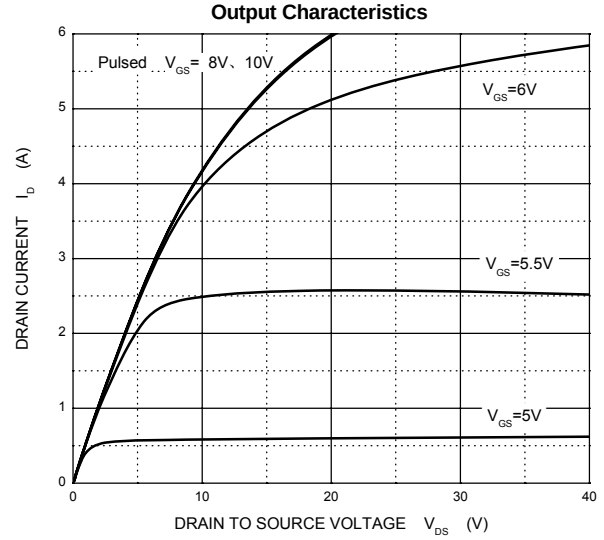
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	600			V
Drain-source diode forward voltage(note2)	V_{SD}	V_{GS} = 0V, I_S =4.0A			1.5	
Zero gate voltage drain current	I_{DSS}	V_{DS} =600V, V_{GS} =0V			25	μA
Gate-body leakage current, forward(note2)	I_{GSSF}	V_{DS} =0V, V_{GS} =30V			100	nA
Gate-body leakage current, reverse(note2)	I_{GSSR}	V_{DS} =0V, V_{GS} =-30V			-100	
On characteristics (note2)						
Gate-threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	2.0	3.5	4.0	V
Static drain-source on-resistance	$R_{DS(on)}$	V_{GS} =10V, I_D =2.0A		1.8	3.0	Ω
Forward transconductance	g_{fs}	V_{DS} =50V, I_D =2A	2.0	2.6		S
Dynamic characteristics (note 3)						
Input capacitance	C_{iss}	V_{DS} =25V,V_{GS} =0V,f =1MHz		540	760	pF
Output capacitance	C_{oss}			125	180	
Reverse transfer capacitance	C_{rss}			8.0	20	
Switching characteristics						
Total gate charge	Q_g	V_{DS} =480V,V_{GS} =10V,I_D =4.0A		5.0	10	nC
Gate-source charge	Q_{gs}			2.7		
Gate-drain charge	Q_{gd}			2.0		
Turn-on delay time (note3)	$t_{d(on)}$	V_{DD}=300V, V_{GS}=10V, R_G=9.1Ω, I_D =4.0A		12	20	ns
Turn-on rise time (note3)	t_r			7.0	10	
Turn-off delay time (note3)	$t_{d(off)}$			19	40	
Turn-off fall time (note3)	t_f			10	20	

Notes :

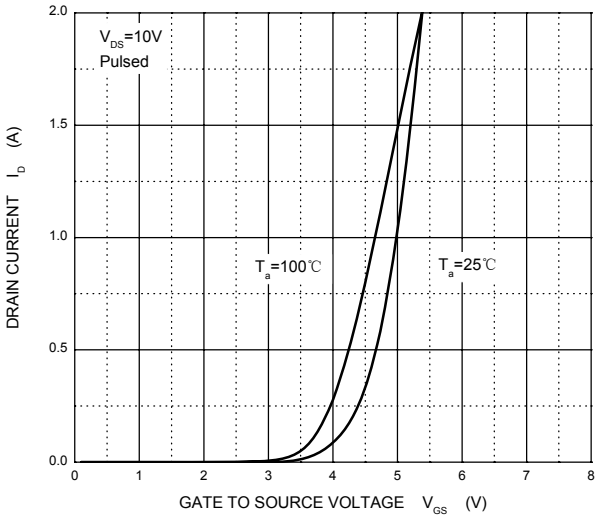
1. L=30mH, I_L=4 A, V_{DD}=100V, V_{GS}=10V,R_G=25Ω,Starting T_J=25℃.
2. Pulse Test : Pulse width≤300μs, duty cycle ≤2%.
3. These parameters have no way to verify.

Typical Characteristics

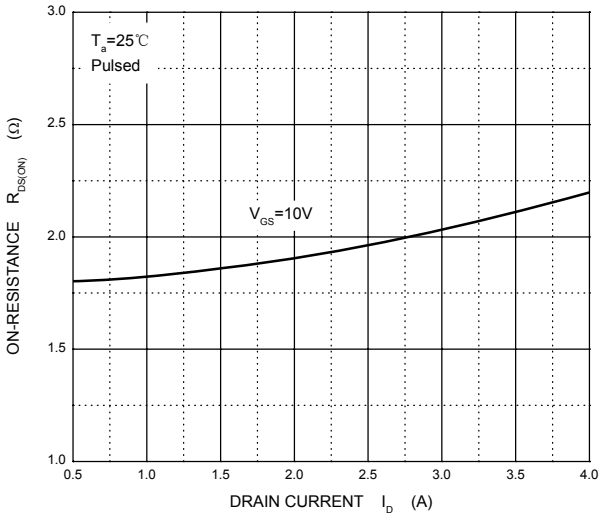
Output Characteristics



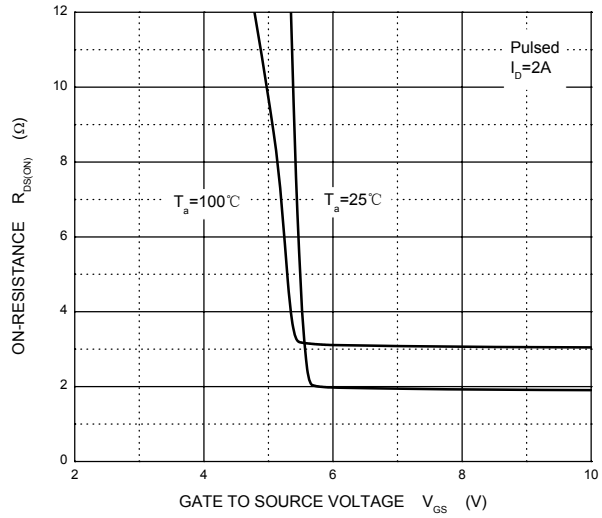
Transfer Characteristics



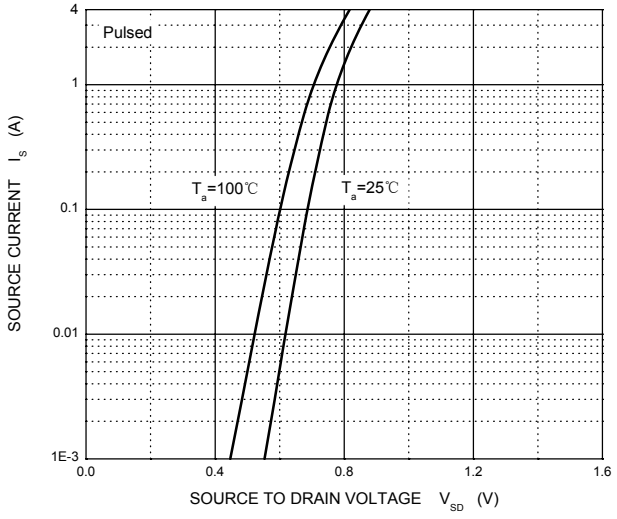
$R_{DS(ON)}$ —— I_D



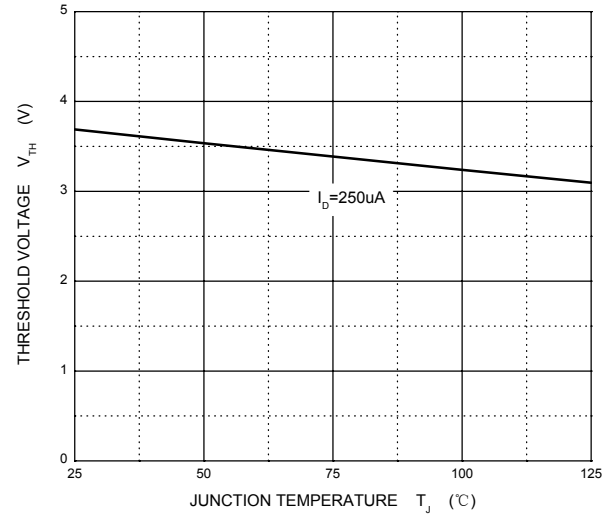
$R_{DS(ON)}$—— V_{GS}



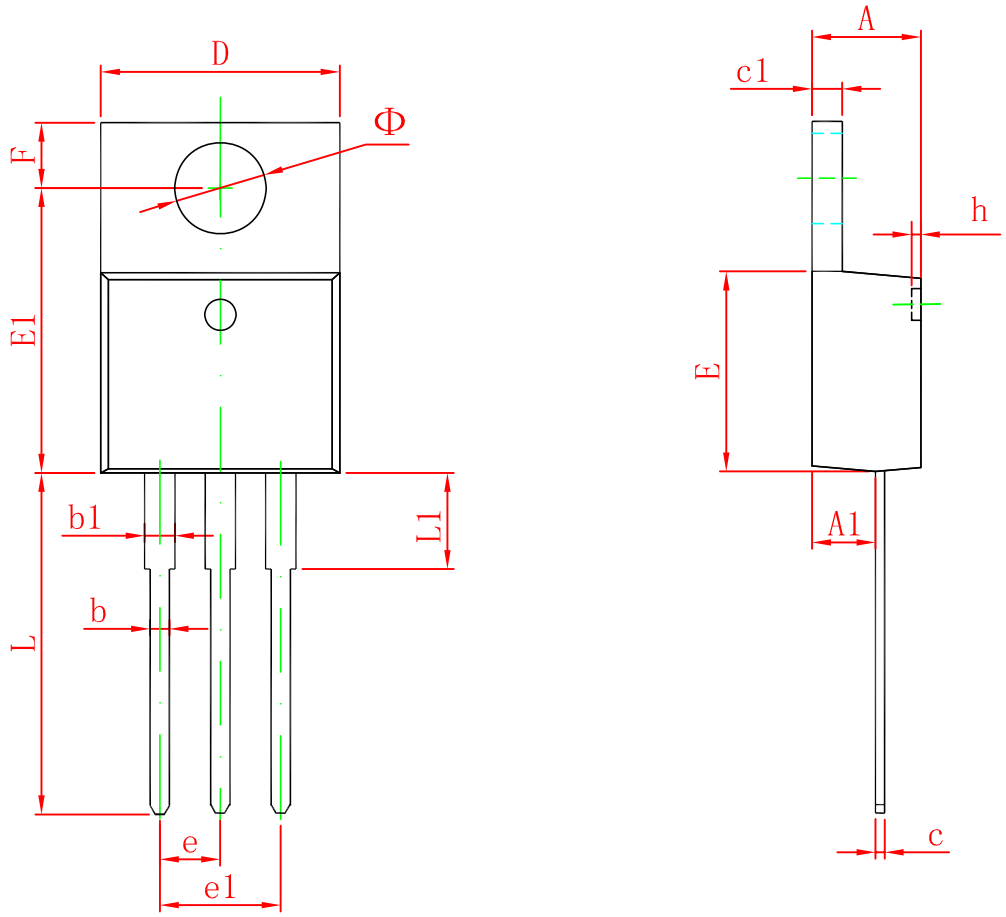
I_S —— V_{SD}



Threshold Voltage



TO-220-3L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.470	4.670	0.176	0.184
A1	2.520	2.820	0.099	0.111
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
E1	12.060	12.460	0.475	0.491
e	2.540 TYP		0.100 TYP	
e1	4.980	5.180	0.196	0.204
F	2.590	2.890	0.102	0.114
h	0.000	0.300	0.000	0.012
L	13.400	13.800	0.528	0.543
L1	3.560	3.960	0.140	0.156
Φ	3.735	3.935	0.147	0.155